

# **PNP** Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 800 mA. Sourced from Process 61.

# Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CES</sub>	Collector-Emitter Voltage	30	V	
V <sub>CBO</sub>	Collector-Base Voltage	30	V	
V <sub>EBO</sub>	Emitter-Base Voltage	10	V	
Ic	Collector Current - Continuous	1.2	A	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These resteady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

# Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units	
		MPSA64	*MMBTA64	**PZTA64	
P <sub>D</sub>	Total Device Dissipation	625	350	1,000	mW
	Derate above 25°C	5.0	2.8	8.0	mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

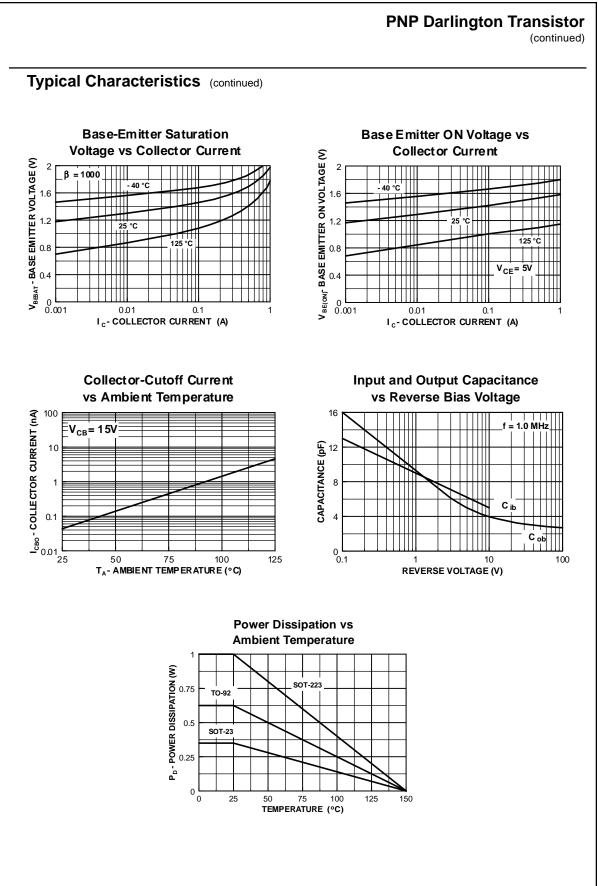
\*\* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

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Symbol	Parameter	Test Conditions	Min	Max	Unit
) FF CHAF	RACTERISTICS				
(BR)CES	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm B} = 0$	30		V
BO	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$		100	nA
BO	Emitter-Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$		100	nA
N CHAR	ACTERISTICS*				
Ē	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000 20,000		
CE(sat)	Collector-Emitter Saturation Voltage	$I_{\rm C}$ = 100 mA, $I_{\rm B}$ = 0.1 mA		1.5	V
BE(on)	Base-Emitter On Voltage	$I_{C}$ = 100 mA, $V_{CE}$ = 5.0 V		2.0	V
	GNAL CHARACTERISTICS	$l_{c} = 10 \text{ mA} \text{ V}_{cr} = 5.0 \text{ V}$	125		MHz
*Pulse Test: Pu NOTE: All volta	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Ilse Width ≤ 300 µs, Duty Cycle ≤ 2.0% ges (V) and currents (A) are negative polarity for PNP t	$I_{C}$ = 10 mA, $V_{CE}$ = 5.0 V, f = 100 MHz ransistors.	125		MH2
*Pulse Test: Pu NOTE: All volta	Current Gain - Bandwidth Product Ilse Width ≤ 300 µs, Duty Cycle ≤ 2.0% ges (V) and currents (A) are negative polarity for PNP t I Characteristics	f = 100 MHz		aturation	
*Pulse Test: Pu NOTE: All volta	Current Gain - Bandwidth Product llse Width $\leq$ 300 µs, Duty Cycle $\leq$ 2.0% ges (V) and currents (A) are negative polarity for PNP t	f = 100 MHz ransistors. <b>Collector</b>	-Emitter Sa		

MPSA64 / MMBTA64 / PZTA64



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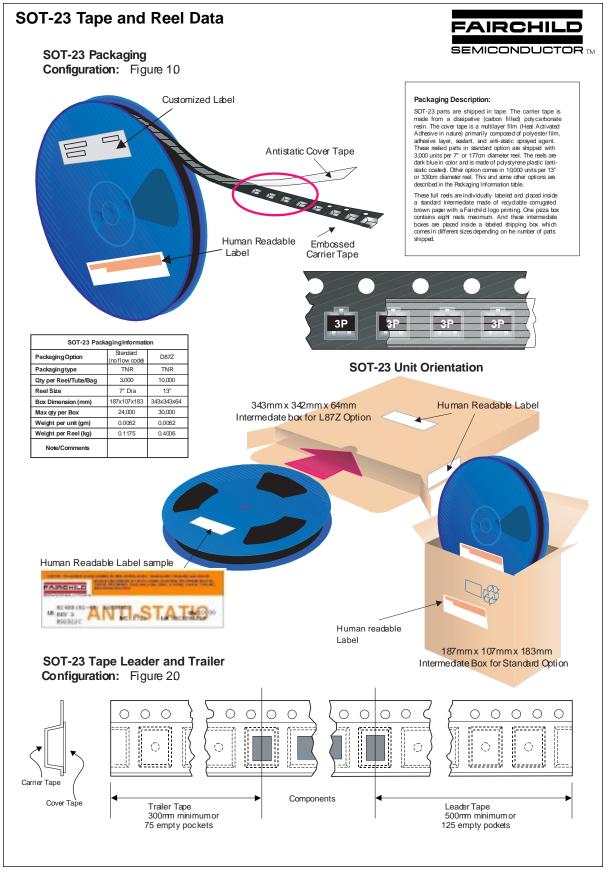
March 2001, Rev. B1





July 1999, Rev. A



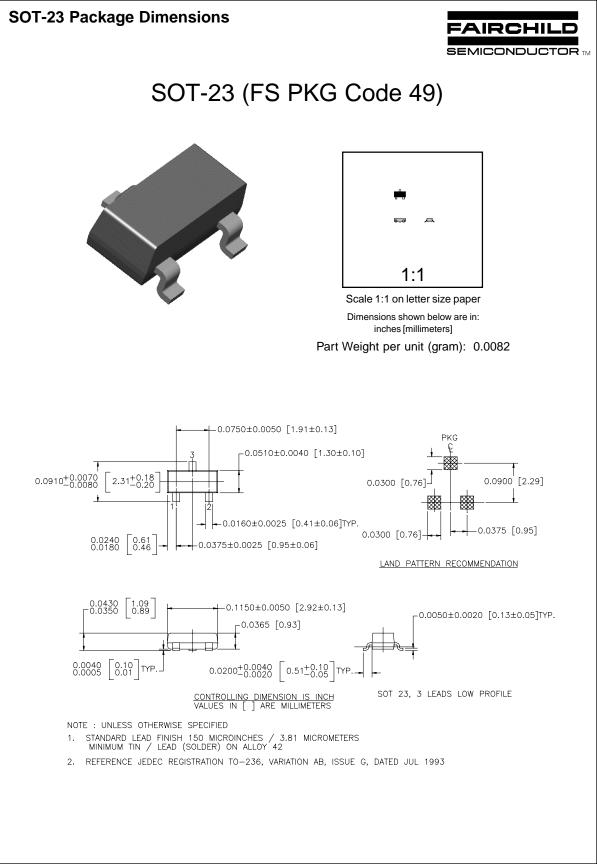


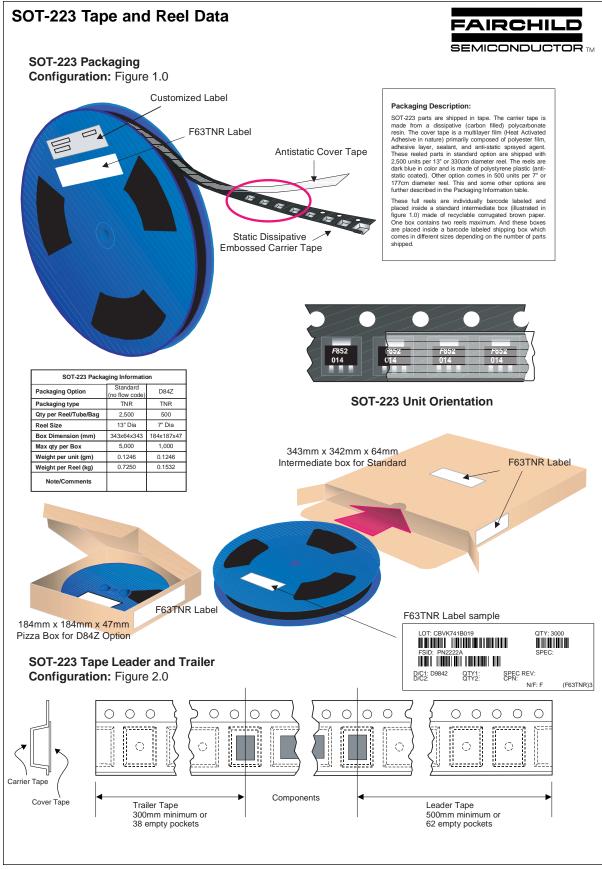
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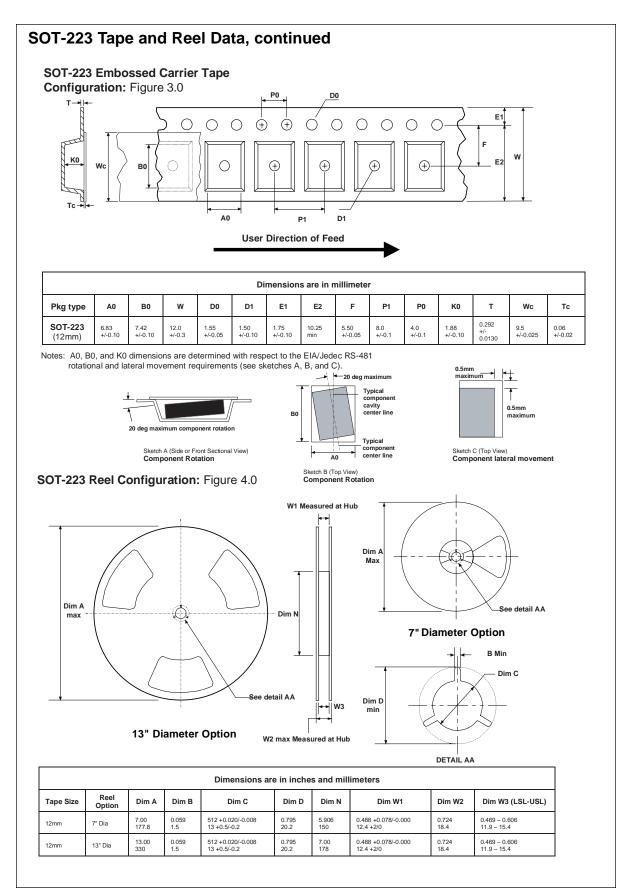
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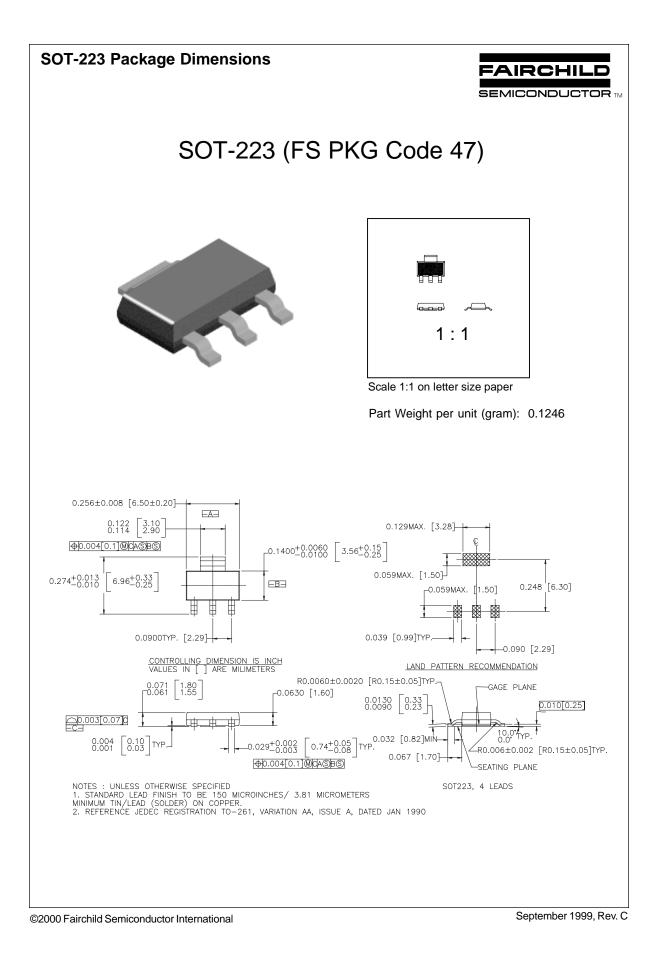




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